

TSMC-02-1226



April 30, 2004

To: Commissioner for Patents
P.O.Box 1450
Alexandria, VA 22313-1450

Fr: George O. Saile, Reg. No. 19,572
28 Davis Avenue
Poughkeepsie, N.Y. 12603

Subject: | Serial No. 10/798,558 03/11/04 |

Yu-Hui Lu et al.

A CALIBRATION STANDARD FOR CRITICAL
DIMENSION VERIFICATION OF SUB-TENTH
MICRON INTEGRATED CIRCUIT TECHNOLOGY

INFORMATION DISCLOSURE STATEMENT

Enclosed is Form PTO-1449, Information Disclosure Citation
In An Application.

The following Patents and/or Publications are submitted to
comply with the duty of disclosure under CFR 1.97-1.99 and
37 CFR 1.56.

CERTIFICATE OF MAILING

I hereby certify that this correspondence is being
deposited with the United States Postal Service as first class
mail in an envelope addressed to: Commissioner for Patents,
P.O. Box 1450, Alexandria, VA 22313-1450, on May 4, 2004.

Stephen B. Ackerman, Reg.# 37761

Signature/Date

Stephen B. Ackerman 5/4/04

U.S. Patent 4,457,803 to Takigawa, "Processing Method Using a Focused Ion Beam," discusses using a focused beam of argon ions to selectively sputter an oxide film.

U.S. Patent 3,988,564 to Garvin et al., "Ion Beam Micromachining Method," discloses a method for fabricating millimeter wave devices.

U.S. Patent 5,945,677 to Leung et al., "Focused Ion Beam System," discloses a focused ion beam (FIB) system which produces a final beam spot size down to 0.1 um or less and an ion beam output current on the order of microamps.

U.S. Patent 6,514,866 to Russell et al., "Chemically Enhanced Focused Ion Beam Micro-Machining of Copper," discloses a method for micro machining a copper film with a focused beam of gallium ions while the film is in an ambient of organic chloride or organic hydroxide vapor.

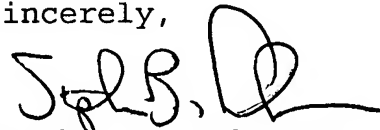
U.S. Patent 5,683,547 to Azuma et al., "Processing Method and Apparatus Using Focused Energy Beam," discloses a method for using a focused energy beam such as an ion beam to assist the local etching of a material with an etchant gas.

U.S. Patent 6,528,818 to Satya et al., "Test Structures and Methods for Inspection of Semiconductor Integrated Circuits," discloses a method for scanning a region on a wafer for defects using a charged particle beam.

U.S. Patent 6,538,844 to Takano et al., "Method of Fabricating a Magnetic Head by Focused Ion Beam Etching," discloses a method for fabricating a magnetic head by focused ion beam etching.

U.S. Patent 5,616,921 to Talbot et al., "Self-Masking FIB Milling," discloses a method for controlling preferential etching during focused ion milling by using a mask image.

Sincerely,

A handwritten signature in black ink, appearing to read "S.B. Ackerman", with a stylized flourish extending to the right.

Stephen B. Ackerman,
Reg. No. 37761

INFORMATION DISCLOSURE CITATION
IN AN APPLICATION

MAY 06 2004

(If several sheets, if necessary)

Docket Number (Optional)

TSMC-02-1226

Application Number

10/798,558

Applicant

Yu-Hui Lu et al.

Filing Date

03/11/04

Drawn At Unit

U. S. PATENT DOCUMENTS

DOCUMENT NUMBER	DATE	TITLE	CLASS	SUBCLASS	PLUNG DATE IF APPROPRIATE
4457803	7/3/84	Takigawa	156	626	12/8/82
3988564	10/26/76	Garvin et al.	219	121 EM	6/14/74
5945677	8/31/99	Leung et al.	250	396 R	1/5/99
6514866	2/4/03	Russell et al.	438	712	5/31/01
5683547	11/4/97	Azuma et al.	156	643.1	7/12/94
6528818	3/4/03	Satya et al.	257	48	8/25/00
6538844	3/25/03	Takano et al.	360	122	2/27/02
5616921	4/1/97	Talbot et al.	250	307	6/30/94

FOREIGN PATENT DOCUMENTS

DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
					YES	NO

OTHER DOCUMENTS (Including Author, Title, Date, Portion of Pages, Etc.)

EXAMINER

DATE CONSIDERED

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.